Silicon NPN Power Transistors 2SC3285

DESCRIPTION

·With TO-3PN package
·High speed switching
·Good linearity of h_{FE}
·High V_{CBO}

APPLICATIONS

·For high speed switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



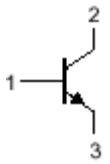


Fig.1 simplified outline (TO-3PN) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		3	A
I_{CP}	Collector current-peak		6	A
I_B	Base current		2	A
P_C	Collector power dissipation	T_C=25□	70	W
		T_a=25□	2.5	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.5A ; I_E=0	800			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=2A; I_B=0.4A			1.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=2A; I_B=0.4A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=1000V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			50	μA
h_{FE}	DC current gain	I_C=2A ; V_{CE}=5V	6			
f_T	Transition frequency	I_C=0.2A ; V_{CE}=5V		4		MHz
Switching times						
t_{on}	Turn-on time	I_C=2A; I_{B1}=0.4A;I_{B2}=-0.8A V_{CC}=250V			1.0	μs
t_s	Storage time				2.5	μs
t_f	Fall time				0.5	μs

PACKAGE OUTLINE

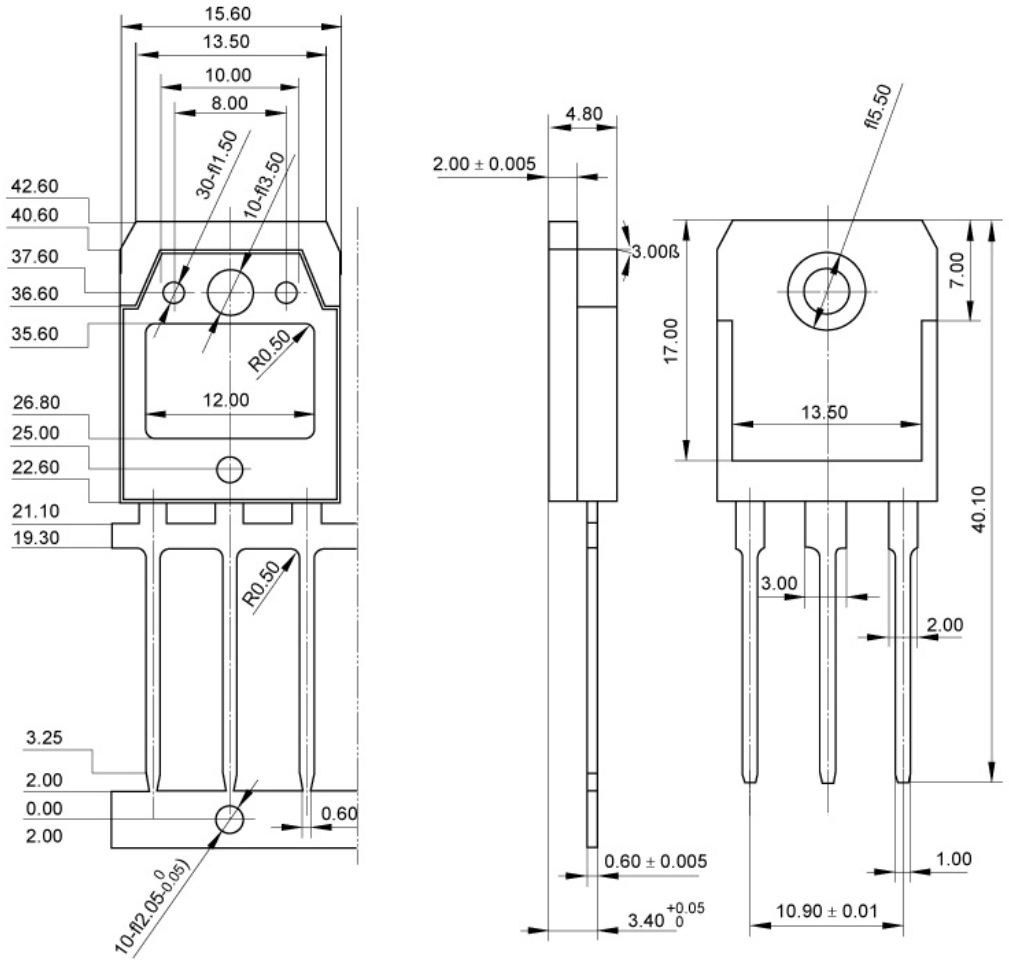


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)